Silicon NPN Power Transistors 2SD950

DESCRIPTION

·With TO-3 package
·Built-in damper diode
·High voltage capability

APPLICATIONS

·Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

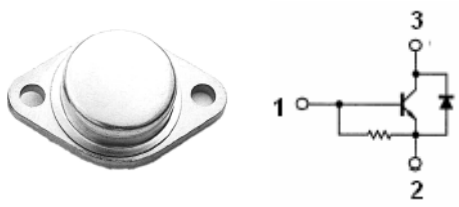

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		4.5	A
P_T	Total power dissipation	T_C=25□	42	W
T_j	Junction temperature		130	□
T_{stg}	Storage temperature		-65~130	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=500m A;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2 A;I_B=0.75 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=2 A;I_B=0.75 A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V;I_E=0			50	μA
		V_{CB}=1500V;I_E=0			1.0	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	8			
h_{FE-2}	DC current gain	I_C=2A ; V_{CE}=10V	3			
V_F	Diode forward voltage	I_F=4A			1.7	V
t_f	Fall time	I_C=2A;I_{Bend}=0.75A;L_B=10μH			0.9	μs
t_s	Storage time			11		μs

PACKAGE OUTLINE

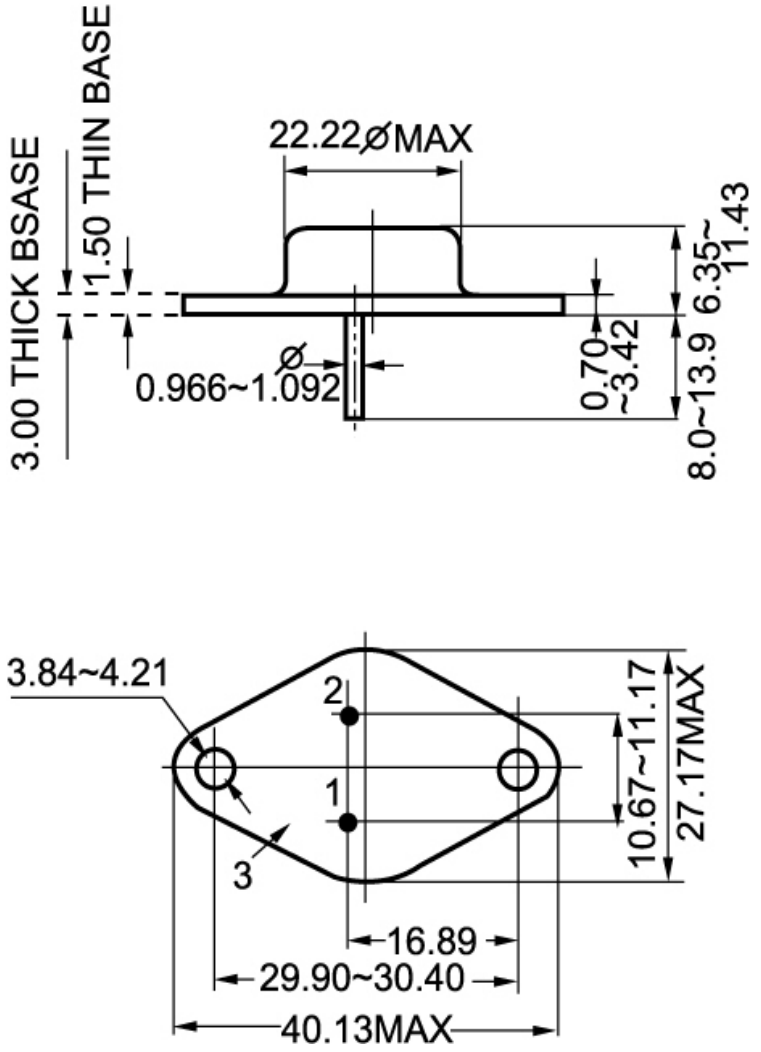

Fig.2 Outline dimensions